

30 V, 200 mA dual P-channel Trench MOSFET

Rev. 1 — 1 August 2011

Product data sheet

1. Product profile

1.1 General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- ESD protection up to 2 kV
- AEC-Q101 qualified
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or					
V _{DS}	drain-source voltage	T _j = 25 °C	-	-	-30	V
V _{GS}	gate-source voltage		-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	<u>[1]</u> _	-	-200	mA
Static chara	cteristics (per transistor)					
R _{DSon}	drain-source on-state resistance	V _{GS} = -4.5 V; I _D = -200 mA; T _i = 25 °C	-	2.8	4.1	Ω

 Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

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2. Pinning information

Table 2.	Pinning	g information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		54 50
2	G1	gate TR1		
3	D2	drain TR2		
4	S2	source TR2		$G1 \xrightarrow{f} G2$
5	G2	gate TR2	1 2 3	
6	D1	drain TR1	SOT363 (SC-88)	
				S1 S2 017aaa260

3. Ordering information

Table 3. O	rdering information	1	
Type numbe	r Package		
	Name	Description	Version
NX3008PBK	S SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 4.	Marking	codes
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Type number	Marking code ^[1]
NX3008PBKS	LC%

[1] % = placeholder for manufacturing site code.

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V _{DS}	drain-source voltage	T _j = 25 °C	-	-30	V
V _{GS}	gate-source voltage		-8	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; \text{ T}_{amb} = 25 \text{ °C}$	<u>[1]</u> _	-200	mA
		$V_{GS} = -4.5 \text{ V}; \text{ T}_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u> _	-125	mA
I _{DM}	peak drain current	$T_{amb} = 25 \text{ °C}; \text{ single pulse}; t_p \le 10 \ \mu\text{s}$	-	-0.8	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2] _	280	mW
			<u>[1]</u> _	320	mW
		T _{sp} = 25 °C	-	990	mW
Per device					
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2] _	445	mW
Tj	junction temperature		-55	150	°C
T _{amb}	ambient temperature		-55	150	°C
T _{stg}	storage temperature		-65	150	°C
Source-dra	ain diode				
I _S	source current	T _{amb} = 25 °C	<u>[1]</u> _	-200	mA
ESD maxir	num rating				
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	2000	V

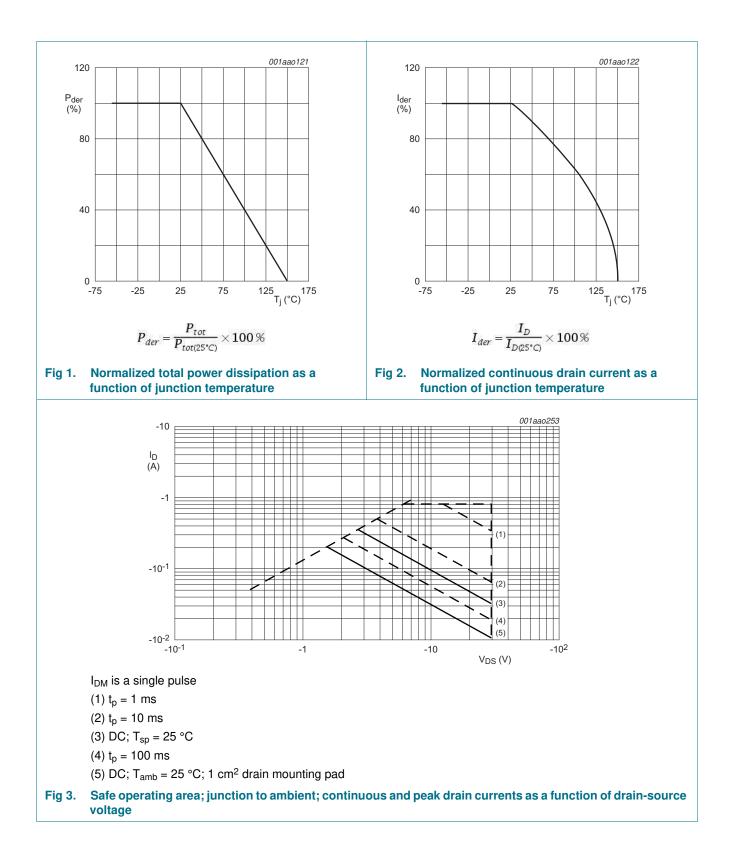
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

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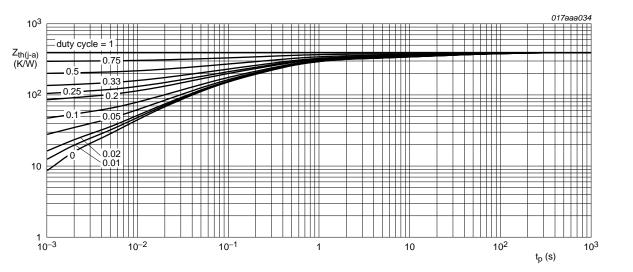
6. Thermal characteristics

	inernial characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	300	K/W
Per transist	or					
R _{th(j-a)}	thermal resistance from junction to	in free air	[1] -	390	445	K/W
	ambient		[2] _	340	390	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	130	K/W

Table 6. Thermal characteristics

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

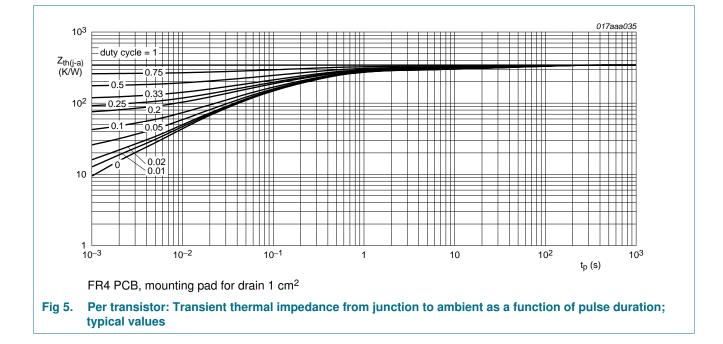


FR4 PCB, standard footprint

Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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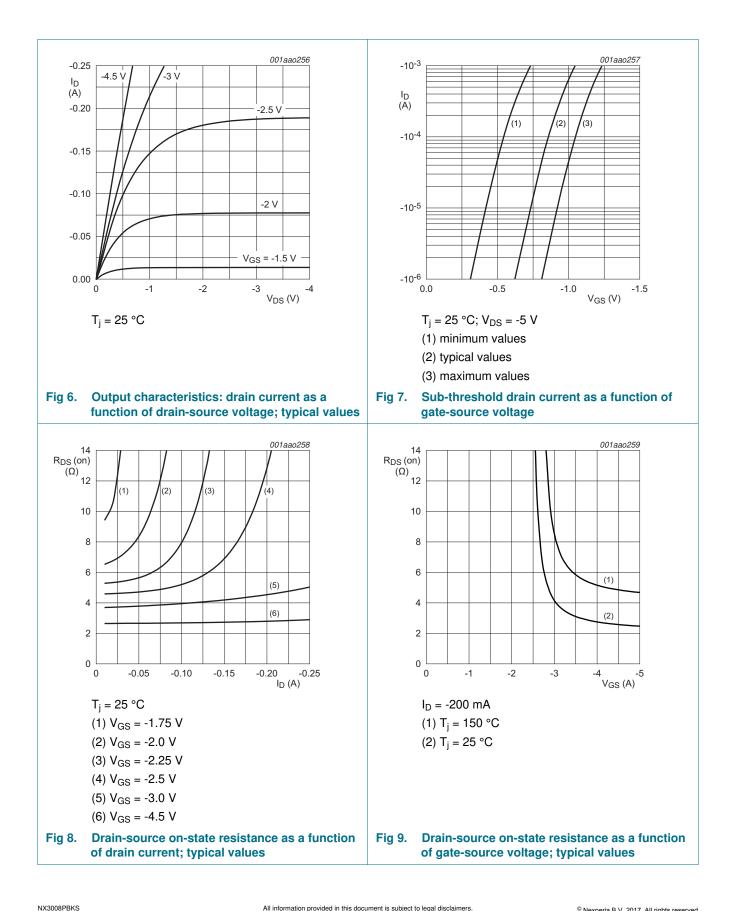
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7. Characteristics

Table 7.	Characteristics	Conditions	P.#!	Tree	Marr	11
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
	racteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C	-30	-	-	V
V _{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^\circ\text{C}$	-0.6	-0.9	-1.1	V
I _{DSS}	drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μA
		$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-0.2	-1	μA
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-0.2	-1	μA
		$V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-10	-	nA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-10	-	nA
		V_{GS} = 2.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-1	-	nA
		V_{GS} = -2.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-1	-	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I _D = -200 mA; T _j = 25 °C	-	2.8	4.1	Ω
	resistance	V_{GS} = -4.5 V; I _D = -200 mA; T _j = 150 °C	-	5.3	7.8	Ω
		V_{GS} = -2.5 V; I _D = -10 mA; T _j = 25 °C	-	5.3	6.5	Ω
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -200 mA; T_{j} = 25 °C	-	160	-	mS
Dynamic o	haracteristics (per transist	or)				
Q _{G(tot)}	total gate charge	$V_{DS} = -15 \text{ V}; I_D = -200 \text{ mA};$	-	0.55	0.72	nC
Q _{GS}	gate-source charge	V _{GS} = -4.5 V; T _j = 25 °C	-	0.23	-	nC
Q _{GD}	gate-drain charge		-	0.09	-	nC
C _{iss}	input capacitance	V_{DS} = -15 V; f = 1 MHz; V_{GS} = 0 V;	-	31	46	pF
C _{oss}	output capacitance	$T_j = 25 \ ^{\circ}C$	-	6.5	-	pF
C _{rss}	reverse transfer capacitance		-	2.3	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -20 V; R_L = 250 Ω; V_{GS} = -4.5 V;	-	19	38	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 \text{ °C}$	-	30	-	ns
t _{d(off)}	turn-off delay time		-	65	130	ns
t _f	fall time		-	38	-	ns
Source-dra	ain diode (per transistor)					
V _{SD}	source-drain voltage	I _S = -200 mA; V _{GS} = 0 V; T _i = 25 °C	-0.47	-0.88	-1.2	V

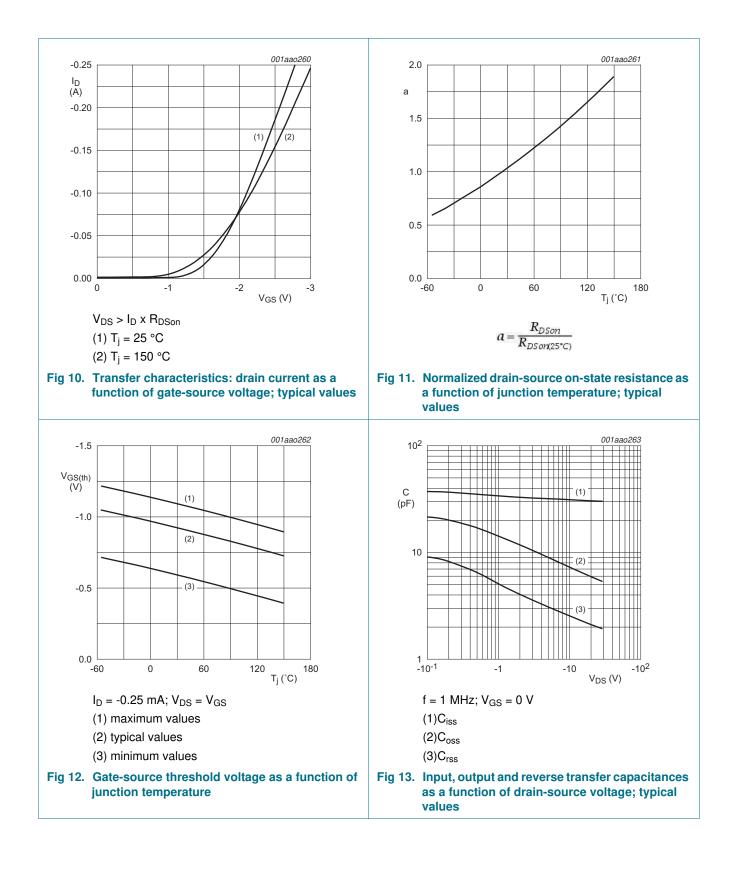
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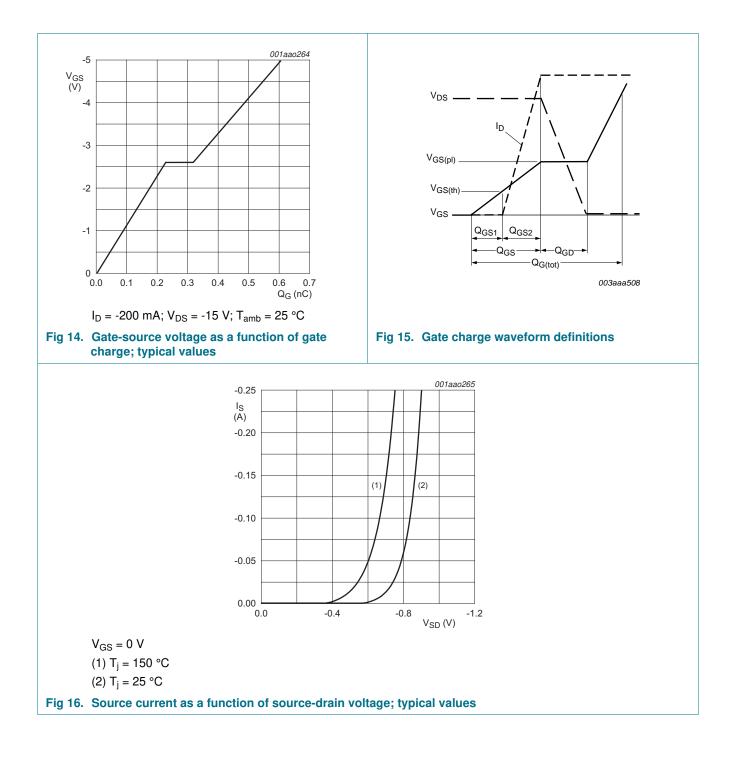
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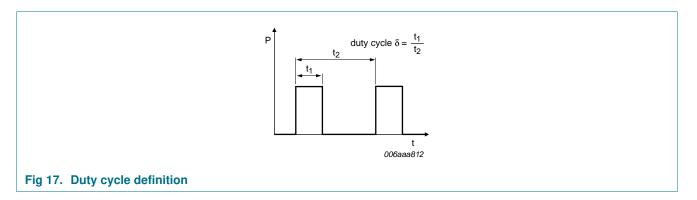
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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline

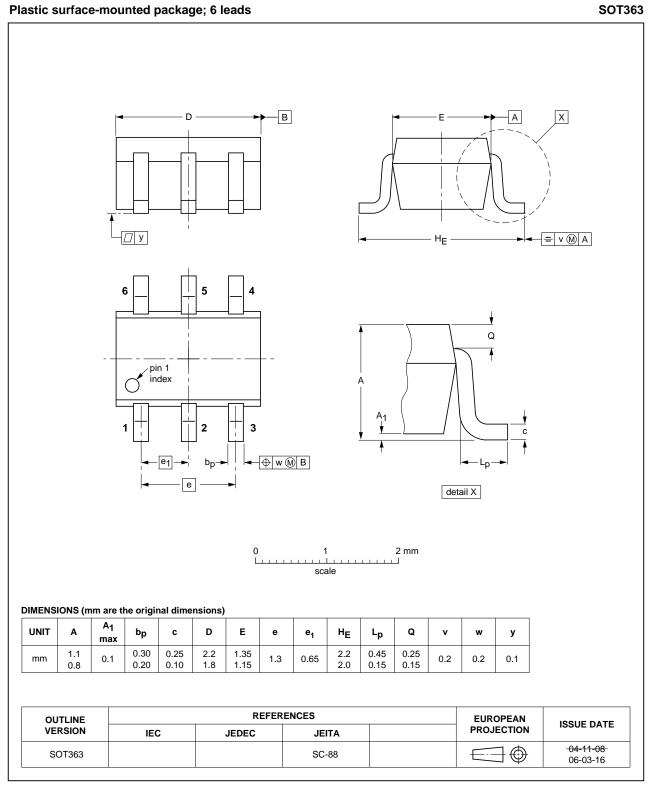


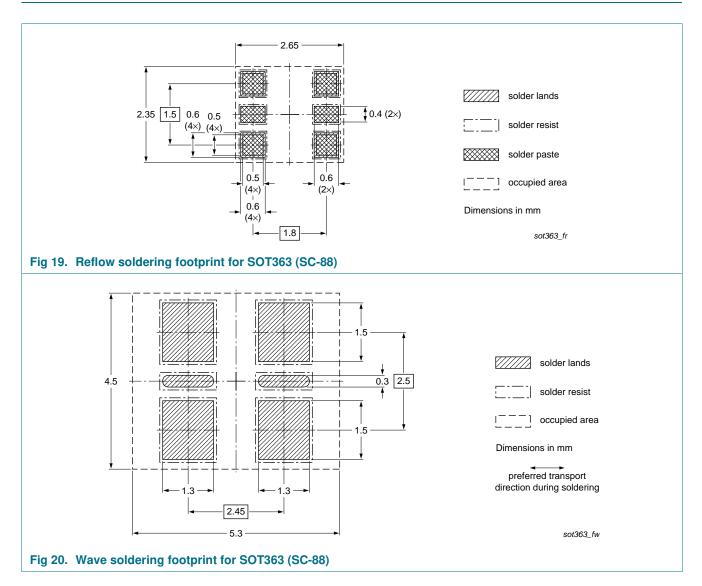
Fig 18. Package outline SOT363 (SC-88)

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10. Soldering



11. Revision history

Table 8. Re	Revision history						
Document ID	I	Release date	Data sheet status	Change notice	Supersedes		
NX3008PBKS	6 v.1	20110801	Product data sheet	-	-		

12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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